



F-6888

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INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				Applicant: Yasuo TARUI, et al.		Filing Date: March 8, 2001	
				Group: 2818			
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
UH		5,978,253	11/2/99	Lee et al.			
UH		6,025,627	2/15/00	Forbes et al.			
UH		5,990,515	11/23/99	Liu et al.			
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
UH		0 940 856	9/8/99	EP			N ^F
TRANSLATION KEY: * English Abstract. ^F Concise statement of relevance provided in foreign search report. ^C Concise statement of relevance provided in specification. ^S Concise statement of relevance provided in IDS. ^P Relevant portion of reference translated. ^O English abstract only - copy of reference in pct search.							
OTHER INFORMATION DISCLOSURE CITATIONS (Including Author, Title, Date, Pertinent Pages, Etc.)							
UH		"Electrical Properties of MFIS-and MFMIS-FETs Using Ferroelectric SrBi ₂ Ta ₂ O ₉ Film and SrTa ₂ O ₆ /SiON Buffer Layer" Extended Abstracts of the International Conference on Solid State Devices and Materials, Japan Society of Applied Physics, Tokyo, Japan; 1999, pages 404-405, XP000935143; *page 405; figure 1*					
EXAMINER	[Signature]			DATE CONSIDERED 03/26/04			
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